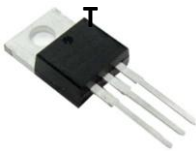
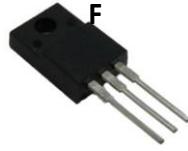


Trench MOS Barrier Schottky Rectifier

TO-220AB
TSR10V100C



ITO-220AB
TSR10V100CT

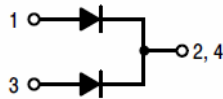


Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes



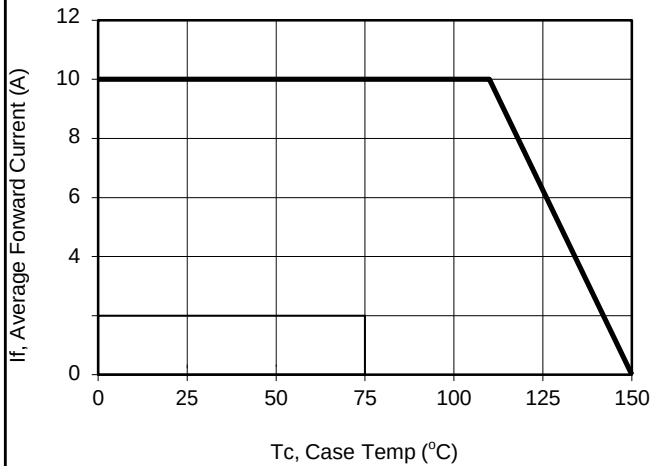
Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Limit		Unit
Maximum repetitive peak reverse voltage			VRRM	100		V
Maximum average forward rectified current	per device		IF(AV)	10		A
	per diode			5		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode			IFSM	120		A
Operating junction and storage temperature range			TJ, TSTG	-65 to +150		°C
Typical thermal resistance per leg	TO-220AB		RθJC	2		°C/W
	ITO-220AB			4		°C/W
Instantaneous forward voltage per diode			VF(1)	TYP.	MAX.	V
	IF=5A	TJ=25°C		-	0.61	
	IF=5A	TJ=125°C		0.42	-	
Instantaneous reverse current per diode at rated reverse voltage	TJ=25°C		IR(2)	-	100	uA
	TJ=125°C			-	20	mA

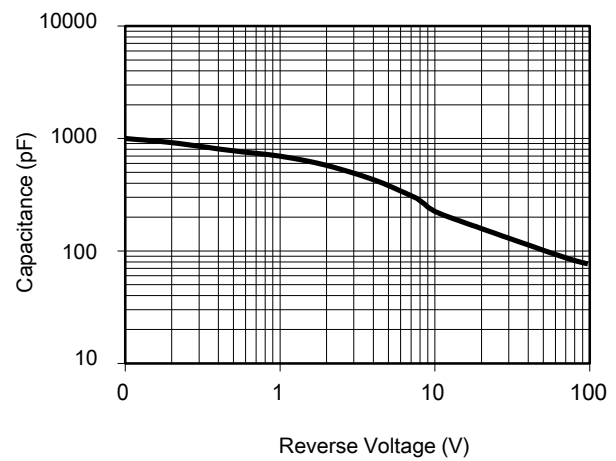
Notes:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

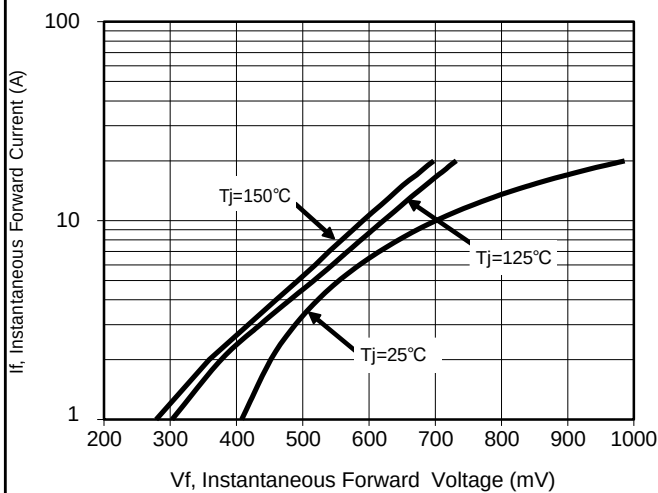
(2) Pulse test: Pulse width ≤ 40 ms

RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)

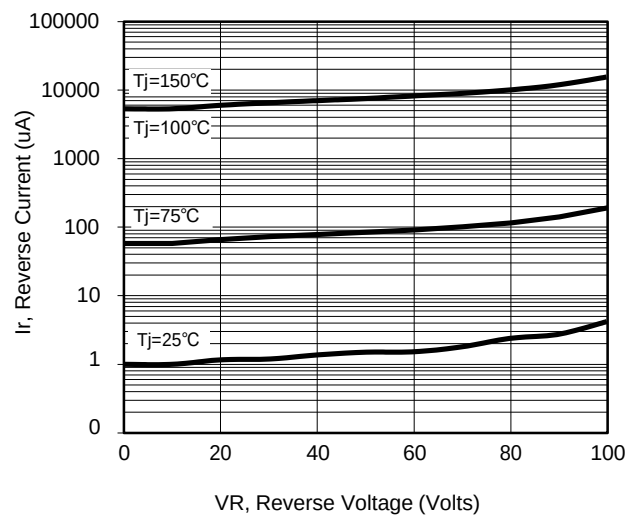
Current Derating, Case



Typical Junction Capacitance



Typical Forward Voltage



Typical Reverse Current

PACKAGE OUTLINE DIMENSIONS

